				ATTY DOCKET NO.		SERIAL NO. 10/519,406			
Form PTO 1449 (Modified)				263098US2X PCT		New U.	S: PCT	F-Application. F/FR03/02225	
•				APPLICANT					
LIST OF	REFEF	RENCES CITED BY API	PLICANT	Lea DI CIOCCIO, et al.		·			
				FILING DATE		GROUP	-010		
		<u></u>		Herewith 01/05/2005			2813	,	
				U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS		LING DATE PPROPRIATE	
O	AA	6 150 239	11/21/00	TONG, Qin-Yistal. Goesele eta	1 438	458			
•	AB								
	AC								
	AD								
	AE								
	AF								
	AG								
	АН							•	
	Al								
	AJ						<u> </u>		
	AK								
	AL								
	AM								
	AN								
			FC	DREIGN PATENT DOCUMENTS	_				
	DOCUMENT DATE COUNTRY					TRANSLATION			
		NUMBER				YES	YES NO		
(Ce)	AO	02 37556	05/10/02	WO(with English abstract)		 		NO	
	AP		 						
	AQ					 		,	
	AR	<u> </u>				 			
	AS					╀		, :	
	AT	ļ · ·	<u> </u>			 			
	AU	<u></u>	<u> </u>	1					
				(Including Author, Title, Date, Pertinent				·	
©	AV	HUGONNARD-BRUYERE E ET AL: "Electrical and physical behavior of SIC layers on insulator (SICOI)" INTERNATIONAL CONFERENCE ON SILICON CARBIDE AND RELATED MATERIALS, ICSRM'99, vol. 338-342, pt. 1, pages 715-718, October 1999.							
œ	AW	HUGONNARD-BRUYERE E ET AL: "Defect Studies in Epitaxial SiC-6H layers on Insulator (SiCOI)" MICROELECTRONIC ENGINEERING, vol. 48, no. 1-4, pages 277-280, September 1999.							
(a)	AX	structures" MATERIAL	HUGONNARD-BRUYERE E ET AL: "Deep level defects in Himplanted 6H-SIC epilayers and in silicon carbide on insulator structures" MATERIAL SCIENCE AND ENGINEERING B, vol. 61-62, pages 382-388, July 30, 1999.						
0	AY	GREGORY R B ET AL: "The effects of damage on hydrogen-implant-induce thin-film seperation from bulk silicon carbide" WIDE-BANDGAP SEMICONDUCTORS FOR HIGH-POWER, HIGH-FREQUENCY AND HIGH-TEMPERATURE APPLICATIONS-1999. SYMPOSIUM, WIDE-BANDGAP SEMICONDUCTORS FOR HIGH-POWER, HIGH-FREQUENCY AND HIGH-TEMPERATURE APPLICATIONS -1999. vol. 572, pages 33-38, 1999.							
(CO)	AZ	BINARI S C ET AL: "H, He, and N implant isolation of n-type GaN" JOURNAL OF APPLIED PHYSICS. vol.78, no. 5, September 1, 1995.				Additional References sheet(s) attached			
Examiner College Considered 29 Jan 2007									
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in									